

INCHANGE SEMICONDUCTOR

iscN-Channel MOSFET Transistor

TK12J55D

RDS(• Enhand Vth = • 100% a • Minimu perform • DESCF • Switchi	ain-source on-resistance: ON) = 0.57 Ω (MAX) cement mode: = 2 to 4V (V _{DS} = 10 V, I _D =1.0mA) avalanche tested Im Lot-to-Lot variations for robust de nance and reliable operation	pin 1.Gate 2.Drain 3.Source TO-3PN package		
SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	550	v	к G + -
V _{GS}	Gate-Source Voltage	±30	V	
ID	Drain Current-Continuous	12	А	
I _{DM}	Drain Current-Single Pulsed	48	A	MIN MAX A 19.60 20.30
PD	Total Dissipation @Tc=25℃	190	w	B 15.50 15.70 C 4.70 4.90 D 0.90 1.10
Tj	Max. Operating Junction Temperature	150	°C	E 1.90 2.10 F 3.40 3.60 G 2.90 3.20
T _{stg}	Storage Temperature	-55~150	°C	H 3.20 3.40 J 0.595 0.605 K 19.80 20.70
• THERM	MAL CHARACTERISTICS	L 1.90 2.20 N 10.89 10.91 Q 4.90 5.10		
SYMBOL	PARAMETER	MAX	UNIT	R 3.35 3.45 S 1.995 2.100
Rth(ch-c)	Channel-to-case thermal resistance	0.658	°C/W	U 5.90 6.20 Y 9.90 10.10



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ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	550			v
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =1.0mA	2		4	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =6A			570	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =550V; V _{GS} = 0V			10	μA
V _{SDF}	Diode forward voltage	I _{DR} =12A, V _{GS} = 0 V			1.7	V



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2